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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		APPLICANT Arup Bhattacharyya	
		PRIORITY FILING DATE February 10, 2003	GROUP 2814 ~~Unknown~~

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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)	APPLICANT Arup Bhattacharyya	
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Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. M122-2506	PRIORITY SERIAL NO. 10/364,710
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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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		Document Number	Date	Country	Class	Subclass	Translation Yes	Translation No
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	AN							
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	AS		
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